



PATENT  
1592-0131P

IN THE U.S. PATENT AND TRADEMARK OFFICE

Applicant: Shigeto FUJIMURA et al. Conf.: 1881  
Appl. No.: 09/753,662 Group: 1765  
Filed: January 4, 2001 Examiner: M.A. Anderson  
For: PROCESS FOR PRODUCING COMPOUND  
SEMICONDUCTOR SINGLE CRYSTAL

REPLY UNDER 37 C.F.R. § 1.111

Assistant Commissioner for Patents  
Washington, DC 20231

June 27, 2002

RECEIVED  
JUN 27 2002  
TECHNOLOGY CENTER  
21700

Sir:

In reply to the Examiner's Office Action dated April 30, 2002, the following amendments and remarks are respectfully submitted in connection with the above-identified application.

IN THE CLAIMS

Please amend claim 1 as follows:

1. (Amended) A process for producing compound semiconductor single crystal, comprising the steps of:

- B<sub>1</sub>
- a) placing a compound semiconductor raw material into a crucible;
  - b) encapsulating the raw material;